

1. Material Substrate GaAlAs (N Type) Removed
Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	V_{F1}		1.1		V	IF=10uA
	V_{F2}		1.4	1.6	V	IF=150mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O	18	21		mW	IF=150mA
Wavelength	λ_P		850		nm	IF=50mA
	$\Delta\lambda$		45		nm	IF=50mA
Rise Time	T_r		11.5		ns	
Fall Time	T_f		6.6		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

- 4. Mechanical Data**
- (a) Emission Area ----- 38.4mil x 38.4mil
 - (b) Bottom Area ----- 39.4mil x 39.4mil
 - (c) Bonding Pad ----- 100um
 - (d) Chip Thickness ----- 7mil
 - (e) Junction Height ----- 6.3mil

